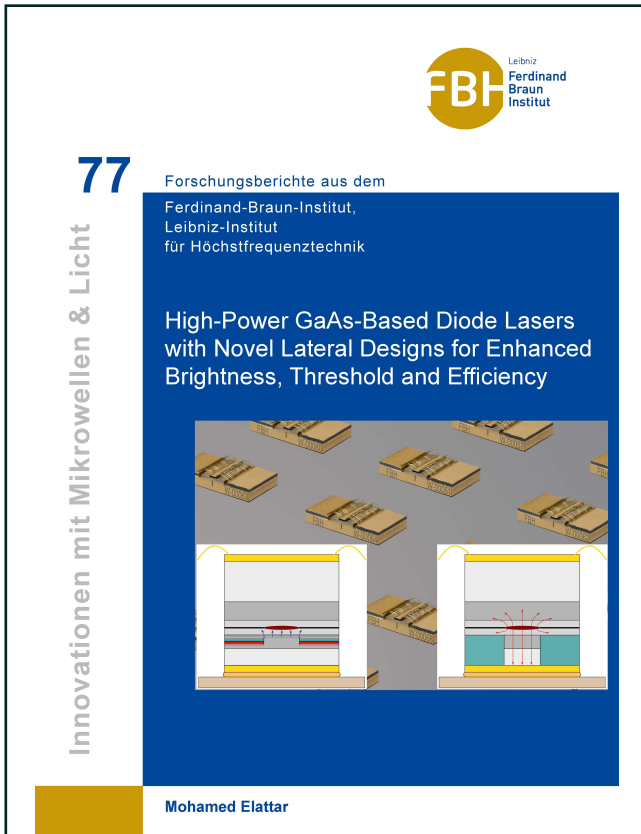




Mohamed Elattar (Autor)

High-Power GaAs-Based Diode Lasers with Novel Lateral Designs for Enhanced Brightness, Threshold and Efficiency



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